

1. General description

The 74LVC2G32 provides a 2-input OR gate function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs in the Power-down mode
- High noise immunity
- ± 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Complies with JEDEC standard:
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Order	ring information						
Type number	Package						
	Temperature range	Name	Description	Version			
74LVC2G32DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2			
74LVC2G32DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1			
74LVC2G32GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1			
74LVC2G32GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089			
74LVC2G32GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2			
74LVC2G32GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2			
74LVC2G32GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116			
74LVC2G32GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203			

4. Marking

Table 2.Marking codes

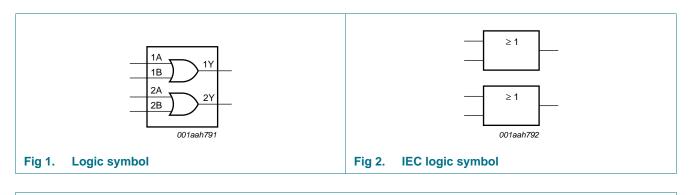
Type number	Marking code ^[1]
74LVC2G32DP	V32
74LVC2G32DC	V32
74LVC2G32GT	V32
74LVC2G32GF	VG
74LVC2G32GD	V32
74LVC2G32GM	V32
74LVC2G32GN	VG
74LVC2G32GS	VG

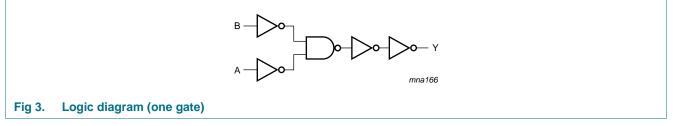
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

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Dual 2-input OR gate

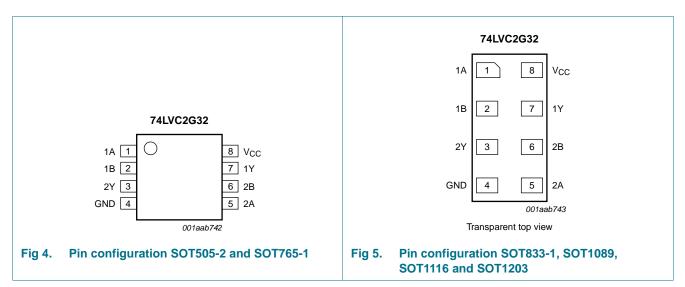
5. Functional diagram



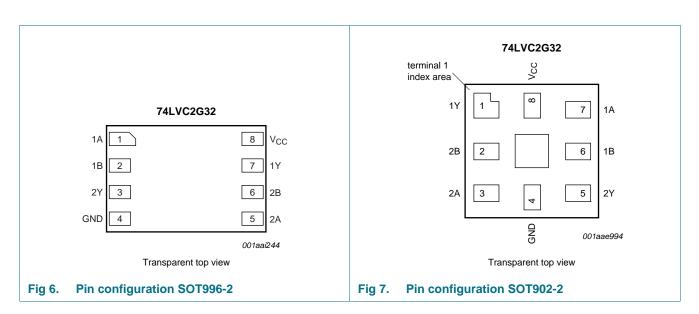


6. Pinning information

6.1 Pinning



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6.2 Pin description

Table 3.	Pin description		
Symbol	Pin	Description	
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2	
1A, 2A	1, 5	7, 3	data input
1B, 2B	2, 6	6, 2	data input
GND	4	4	ground (0 V)
1Y, 2Y	7, 3	1, 5	data output
V _{CC}	8	8	supply voltage

7. Functional description

Table 4.	Function table [1]		
Input			Output
nA		nB	nY
L		L	L
L		Н	Н
Н		L	Н
Н		Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
Vo	output voltage	Active mode	<u>[1]</u> –0.5	V _{CC} + 0.5	V
		Power-down mode	[2] -0.5	+6.5	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
Ι _{ΟΚ}	output clamping current	$V_O < 0 V \text{ or } V_O > V_{CC}$	-	±50	mA
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	[3] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal condition.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
 For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
 For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	-	10	ns/V

Dual 2-input OR gate

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -4	40 °C to +85 °C <u>[1]</u>					
VIH	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = -100 \ \mu\text{A}; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	$V_{CC}-0.1$	-	-	V
		$I_0 = -4$ mA; $V_{CC} = 1.65$ V	1.2	1.53	-	V
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	2.13	-	V
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	2.50	-	V
		$I_0 = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	2.60	-	V
		$I_0 = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	4.10	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	0.08	0.45	V
		$I_0 = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	0.14	0.3	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	0.19	0.4	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.37	0.55	V
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.43	0.55	V
l _l	input leakage current	V_{I} = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	±0.1	±5	μΑ
I _{OFF}	power-off leakage current	V_1 or V_0 = 5.5 V; V_{CC} = 0 V	-	±0.1	±10	μΑ
I _{CC}	supply current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V; I _O = 0 A	-	0.1	10	μA
Δl _{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	5	500	μA
Ci	input capacitance		-	2.5	-	pF
T _{amb} = -4	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
	-	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7\times V_{CC}$	-	-	V
VIL	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
	· •	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	V
		$V_{CC} = 4.5 V \text{ to } 5.5 V$	-	-	$0.3 \times V_{CC}$	V

Dual 2-input OR gate

At recom	At recommended operating conditions; voltages are referenced to GND (ground = 0 V).							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$						
		I_{O} = –100 $\mu\text{A};$ V_{CC} = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	V		
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V		
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V		
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V		
		$I_0 = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	-	-	V		
		$I_0 = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.4	-	-	V		
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$						
		I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V		
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V		
		$I_0 = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V		
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V		
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V		
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V		
I _I	input leakage current	V_{I} = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±20	μA		
I _{OFF}	power-off leakage current	V_1 or V_0 = 5.5 V; V_{CC} = 0 V	-	-	±20	μA		
I _{CC}	supply current	$V_{\rm I}$ = 5.5 V or GND; $V_{\rm CC}$ = 1.65 V to 5.5 V; $I_{\rm O}$ = 0 A	-	-	40	μΑ		
ΔI_{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5000	μΑ		

Table 7. Static characteristics ... continued

[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. **Dynamic characteristics**

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	-4	–40 °C to +85 °C			–40 °C to +125 °C	
			Min	Typ <mark>[1]</mark>	Мах	Min	Max]
t _{pd} propagation delay		nA, nB to nY; see Figure 8	<u>2]</u>					
	V_{CC} = 1.65 V to 1.95 V	1.3	3.9	8.8	1.3	11	ns	
		V_{CC} = 2.3 V to 2.7 V	0.8	2.4	4.7	0.8	5.9	ns
		$V_{CC} = 2.7 V$	0.8	2.7	4.8	0.8	6.0	ns
		V_{CC} = 3.0 V to 3.6 V	0.9	2.2	4.2	0.9	5.3	ns
		V_{CC} = 4.5 V to 5.5 V	0.7	1.7	3.2	0.7	4.0	ns

Voltages a	Voltages are referenced to GND (ground 0 V); for test circuit see <u>Figure 9</u> .								
Symbol	Parameter	Conditions		–40 °C to +85 °C		–40 °C to +125 °C		Unit	
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
C _{PD}	power dissipation capacitance	per gate; $V_I = GND$ to V_{CC}	<u>[3]</u>	-	14	-	-	-	pF

Table 8. Dynamic characteristics ... continued

[1] Typical values are measured at nominal V_{CC} and at $T_{amb} = 25$ °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms

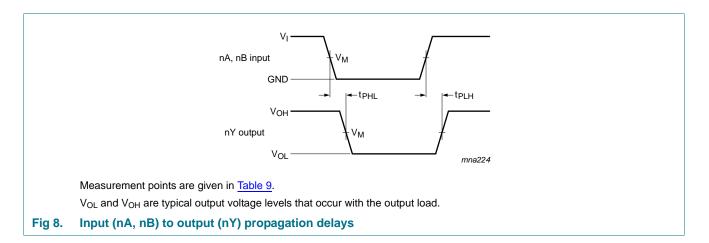


Table 9. **Measurement points**

Supply voltage	Input	Output
V _{cc}	V _M	V _M
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}
2.3 V to 2.7 V	0.5V _{CC}	0.5V _{CC}
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5V _{CC}	0.5V _{CC}

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Dual 2-input OR gate

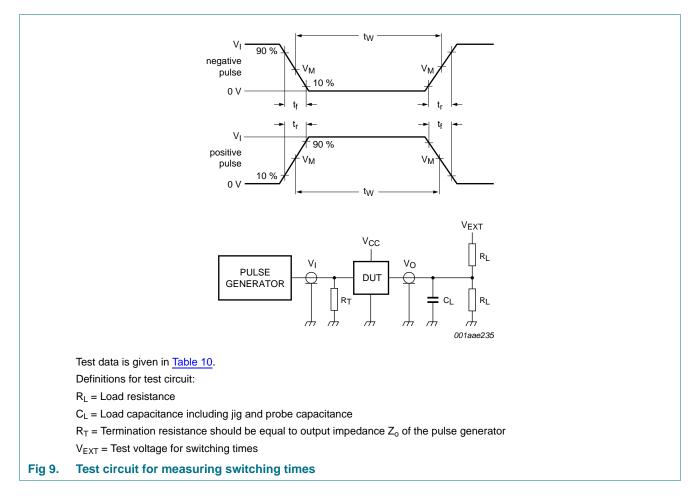
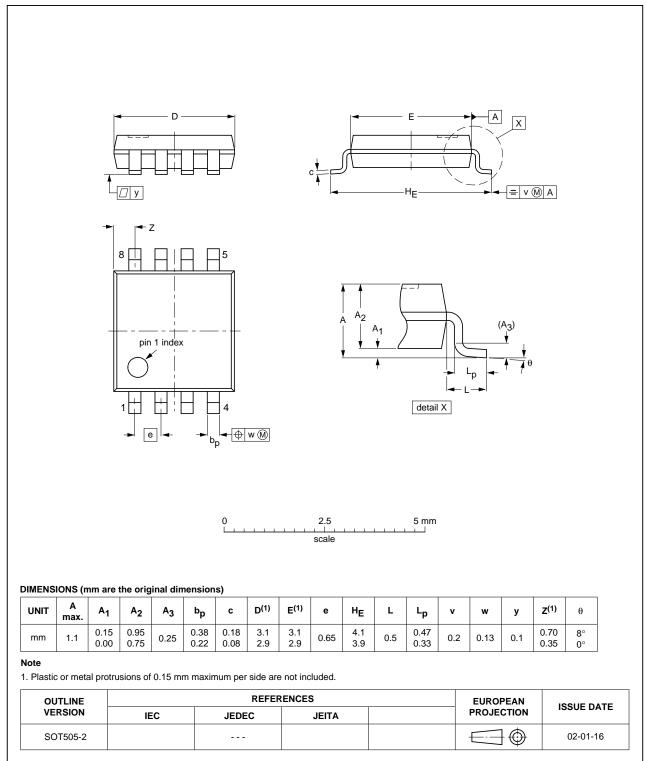


Table 10. Test data

Supply voltage	Input		Load		V _{EXT}
V _{cc}	VI	t _r , t _f	CL	RL	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V _{CC}	\leq 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V _{CC}	\leq 2.5 ns	50 pF	500 Ω	open

13. Package outline



TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

Fig 10. Package outline SOT505-2 (TSSOP8)

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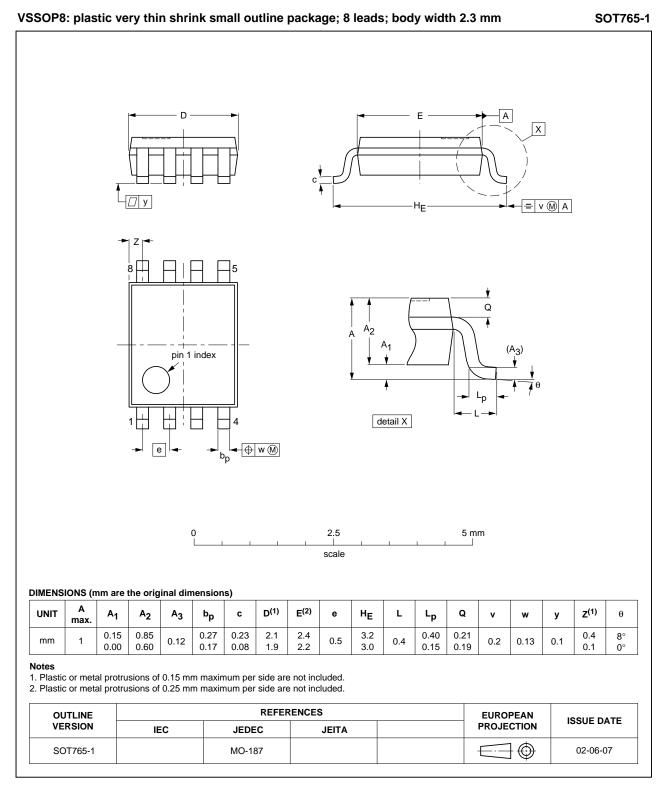


Fig 11. Package outline SOT765-1 (VSSOP8)

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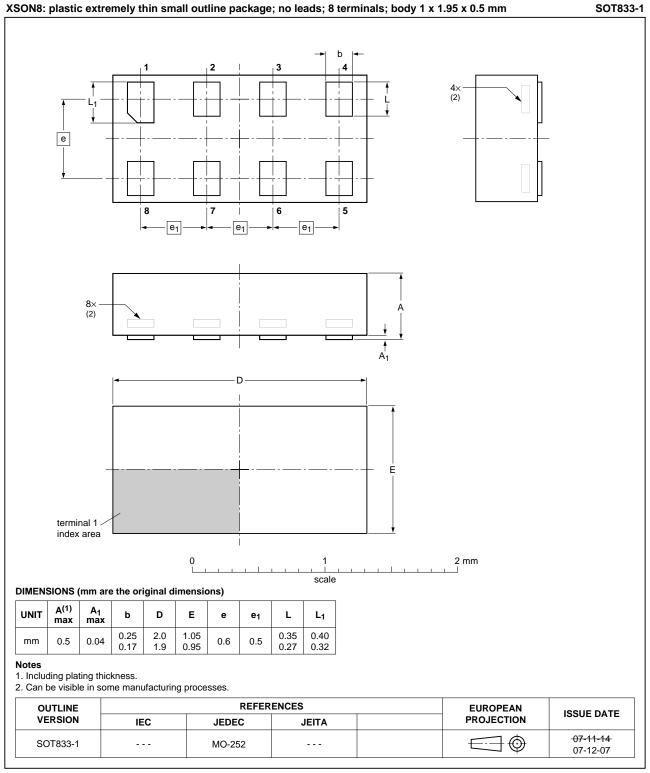
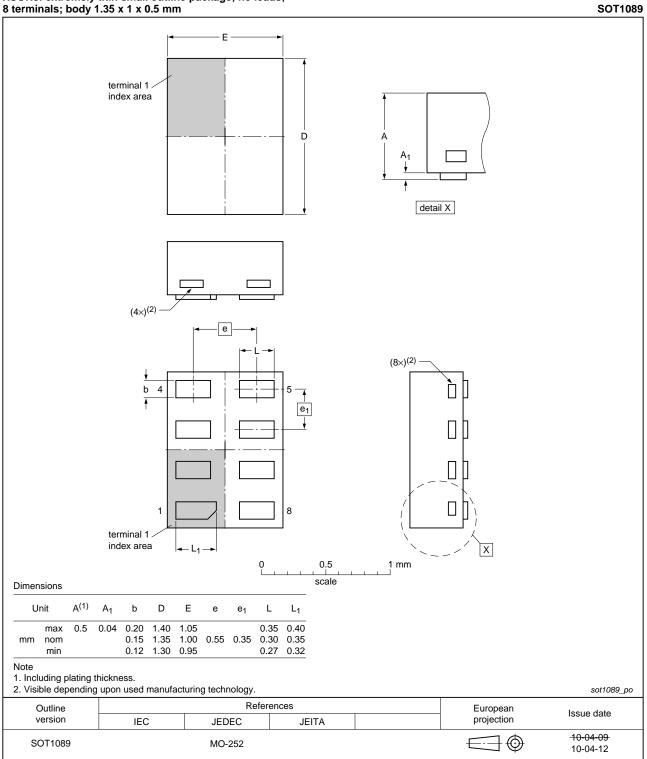


Fig 12. Package outline SOT833-1 (XSON8)

74LVC2G32

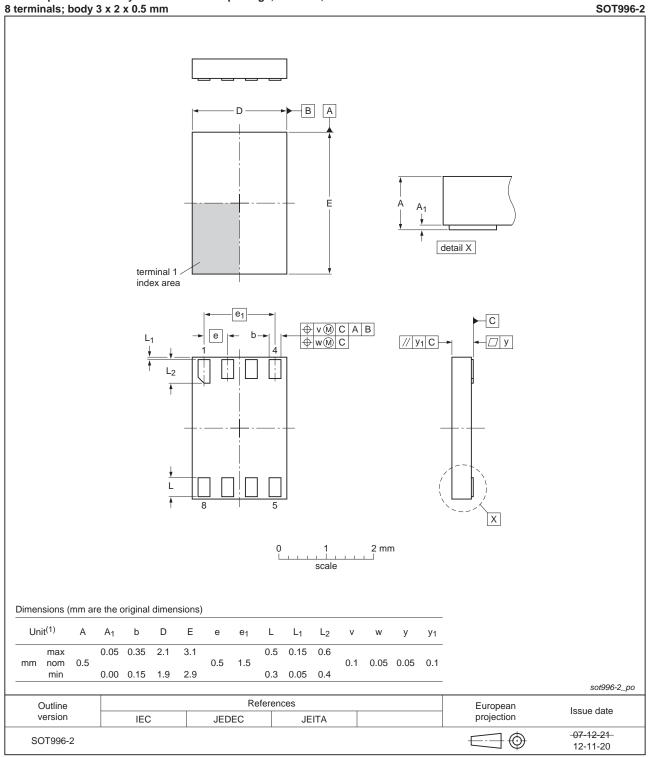
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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 13. Package outline SOT1089 (XSON8)

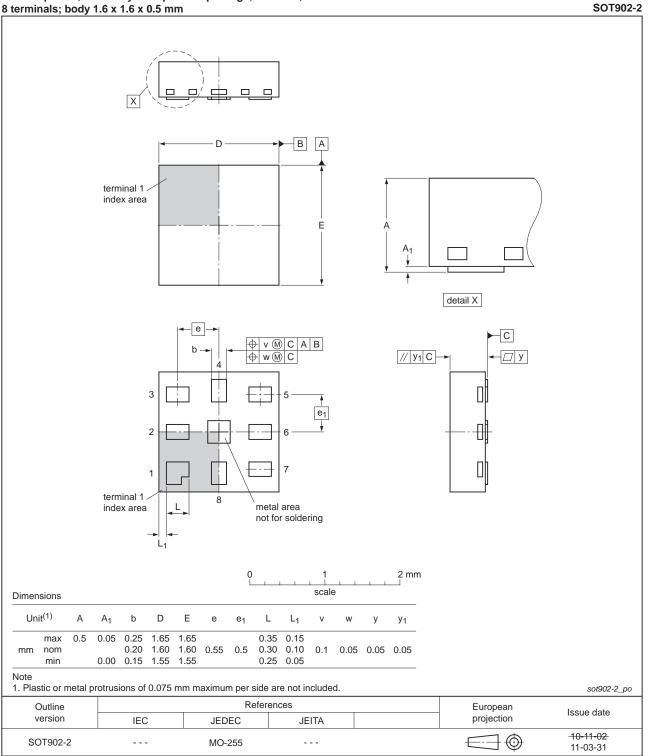
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XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm

Fig 14. Package outline SOT996-2 (XSON8)

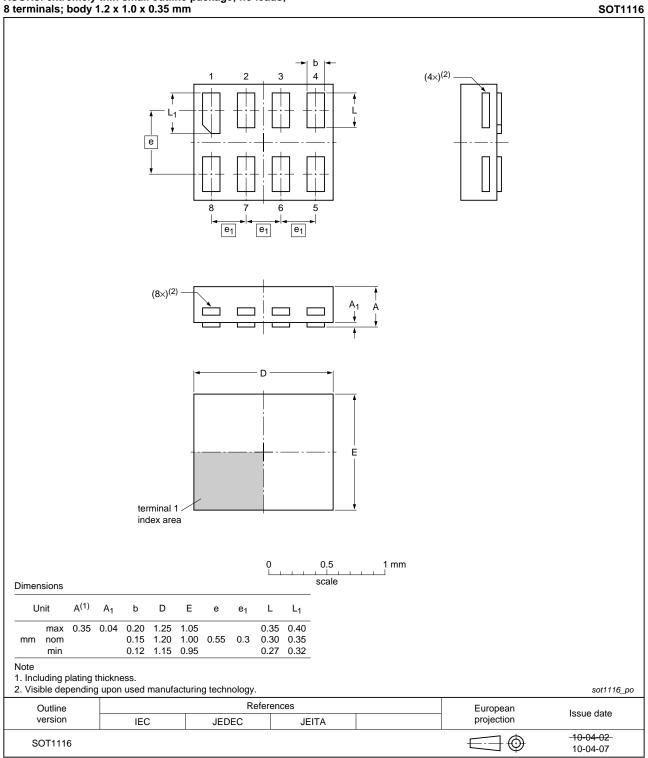
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XQFN8: plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

Fig 15. Package outline SOT902-2 (XQFN8)

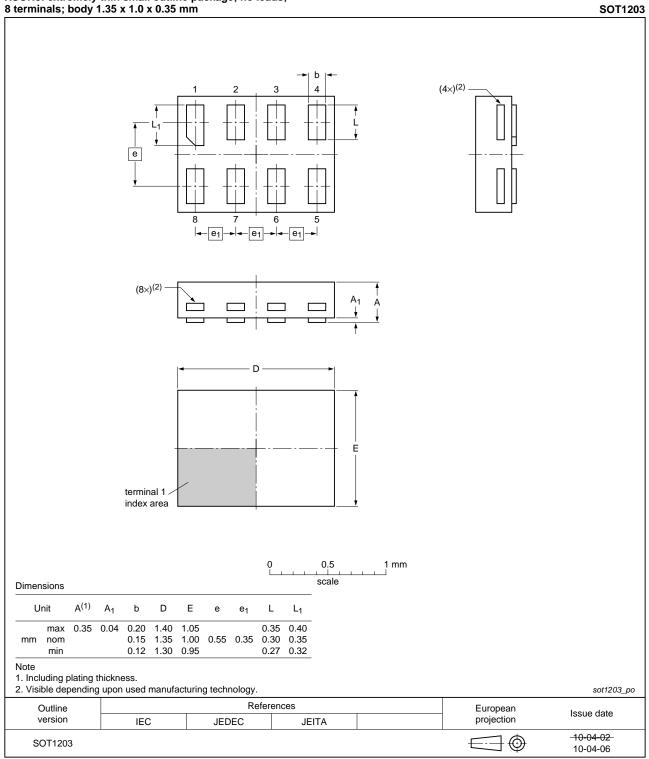
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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1116 (XSON8)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1203 (XSON8)

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14. Abbreviations

Acronym CMOS	Description
CMOS	Complementary Matel Ovide Comisen duster
01000	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G32v.11	20130408	Product data sheet	-	74LVC2G32 v.10
Modifications:	 For type nu 	mber 74LVC2G32GD XSO	N8U has changed to XS	SON8.
74LVC2G32 v.10	20120622	Product data sheet	-	74LVC2G32 v.9
Modifications:	 For type nu 	mber 74LVC2G32GM the S	OT code has changed	to SOT902-2.
74LVC2G32 v.9	20111128	Product data sheet	-	74LVC2G32 v.8
Modifications:	 Legal pages 	s updated.		
74LVC2G32 v.8	20101110	Product data sheet	-	74LVC2G32 v.7
74LVC2G32 v.7	20080606	Product data sheet	-	74LVC2G32 v.6
74LVC2G32 v.6	20080227	Product data sheet	-	74LVC2G32 v.5
74LVC2G32 v.5	20070904	Product data sheet	-	74LVC2G32 v.4
74LVC2G32 v.4	20060515	Product data sheet	-	74LVC2G32 v.3
74LVC2G32 v.3	20050201	Product specification	-	74LVC2G32 v.2
74LVC2G32 v.2	20040922	Product specification	-	74LVC2G32 v.1
74LVC2G32 v.1	20031027	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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